

DUAL N CHANNEL MOSFET, 20V, Transistor Polarity: Dual N Channel, Continuous Drain Current Id: 630mA, Drain Source Voltage Vds: 20V, On Resistance Rds(on): 0.29ohm, Rds(on) Test Voltage Vgs: 4.5V, Threshold Voltage Vgs: 920mV

Manufacturers	<a href="#">ON Semiconductor, LLC</a>
Package/Case	SC-88
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for NTJD4401NT1G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

This N-Channel dual device was designed with a small footprint package (2x2 mm) with ON Semiconductor's leading planar process for small footprint and increased efficiency. The low figure of merit is particularly suited for single or dual cell Li-Ion battery supplied devices such as cell phones, media players, digital cameras, and PDAs.

## Features

- Small Footprint (2 x 2 mm)
- Low Gate Charge N-Channel Device
- ESD Protected Gate
- Same Package as SC-70 (6 Leads)
- RoHS Compliant

## Application

ONSEMI

## Related Products



### [NTR4003NT3G](#)

ON Semiconductor, LLC  
SOT-23



### [NTD2955G](#)

ON Semiconductor, LLC  
TO-252



[NTZD3155CT2G](#)

ON Semiconductor, LLC  
SOT-563-6



[NTR5103NT1G](#)

ON Semiconductor, LLC  
SOT-23



[NTHD4102PT1G](#)

ON Semiconductor, LLC  
ChipFET-8



[NTS2101PT1G](#)

ON Semiconductor, LLC  
SOT-323



[NTMFS4C10NT1G](#)

ON Semiconductor, LLC  
SO-8FL



[NTH4L020N120SC1](#)

ON Semiconductor, LLC  
TO-247